DC COMPONENTS CO., LTD.

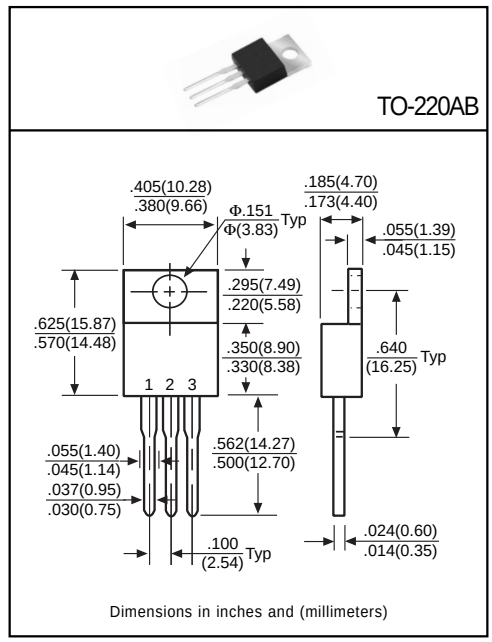
DISCRETE SEMICONDUCTORS

2SB857

TECHNICAL SPECIFICATIONS OF PNP EPITAXIAL PLANAR TRANSISTOR

Description

Designed for low frequency power amplifier.



Pinning

1 = Base
2 = Collector
3 = Emitter

Absolute Maximum Ratings(T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-70	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current (continuous)	I_C	-4	A
Collector Current (peak)	I_C	-8	A
Total Power Dissipation(T_C=25°C)	P_D	40	W
Junction Temperature	T_J	+150	°C
Storage Temperature	T_{STG}	-55 to +150	°C

Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Volatge	BV_{CBO}	-70	-	-	V	I_C=-10μA, I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-50	-	-	V	I_C=-50mA, I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	-	-	V	I_E=-10μA, I_C=0
Collector Cutoff Current	I_{CBO}	-	-	-1	μA	V_{CB}=-50V, I_E=0
Collector-Emitter Saturation Voltage(1)	$V_{CE(sat)}$	-	-	-1	V	I_C=-2A, I_B=-0.2A
Base-Emitter On Voltage(1)	$V_{BE(on)}$	-	-	-1	V	I_C=-1A, V_{CE}=-4V
DC Current Gain(1)	h_{FE1}	35	-	-	-	I_C=-0.1A, V_{CE}=-4V
	h_{FE2}	60	-	320	-	I_C=-1A, V_{CE}=-4V
Transition Frequency	f_T	-	15	-	MHz	I_C=-500mA, V_{CE}=-4V, f=100MHz

(1)Pulse Test: Pulse Width ≦ 380μs, Duty Cycle ≦ 2%

Classification of h_{FE2}

Rank	B	C	D
Range	60~120	100~200	160~320